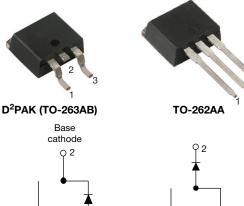
www.vishay.com

VS-MURB1520-M3, VS-MURB1520-1-M3

Vishay Semiconductors

Ultrafast Rectifier, 15 A FRED Pt[®]



ქ 3 ሰ N/C Anode

3 ბ1 N/C Anode

VS-MURB1520-M3

VS-MURB1520-1-M3

PRIMARY CHARACTERISTICS					
I _{F(AV)}	15 A				
V _R	200 V				
V _F at I _F	0.85 V				
t _{rr}	35 ns				
T _J max.	175 °C				
Package	D ² PAK (TO-263AB), TO-262AA				
Circuit configuration	Single				

FEATURES

- · Ultrafast recovery time
- · Low forward voltage drop
- Low leakage current
- 175 °C operating junction temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

MUR.. series are the state of the art ultrafast recovery rectifiers specifically designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS				
Peak repetitive reverse voltage	V _{RRM}		200	V				
Average rectified forward current	I _{F(AV)}	Total device, rated V_R , $T_C = 150 \ ^\circ C$	15					
Non-repetitive peak surge current	I _{FSM}		200	А				
Peak repetitive forward current	I _{FM}	Rated V _R , square wave, 20 kHz, T _C = 150 °C	30					
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C				

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	200	-	-	V	
Ferrura veltere	V _F	I _F = 15 A	-	-	1.05	V	
Forward voltage		I _F = 15 A, T _J = 150 °C	-	-	0.85		
Deverse leekerse ourrent		$V_{\rm R} = V_{\rm R}$ rated	-	-	10		
Reverse leakage current	I _R	$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	-	500	μΑ	
Junction capacitance	CT	V _R = 200 V	-	55	-	pF	
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH	

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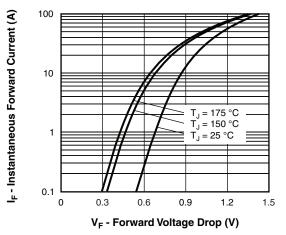


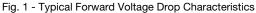
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DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS	
			50 A/µs, V _R = 30 V	-	-	35		
Reverse recovery time	t _{rr}	T _J = 25 °C		-	22	-	ns	
		T _J = 125 °C		-	39	-		
Peak recovery current	I _{RRM}	I	T _J = 25 °C	l _F = 15 A dl _F /dt = 200 A/µs	-	1.6	-	А
Feak recovery current		T _J = 125 °C	$V_{\rm B} = 160 \text{V}$	-	4.1	-	~	
	0	T _J = 25 °C	v _R = 100 v	-	19	-	nC	
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	90	-	no	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C
Thermal resistance, junction-to-case	R _{thJC}		-	-	1.5	
Thermal resistance, junction-to-ambient	R _{thJA}		-	-	50	°C/W
Thermal resistance, case-to-heatsink	R _{thCS}	Mounting surface, flat, smooth, and greased	-	0.5	-	
Weight			-	2.0	-	g
Weight			-	0.07	-	oz.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking dovice		Case style D ² PAK (TO-263AB)	MURB1520			
Marking device		Case style TO-262		MURB	1520-1	





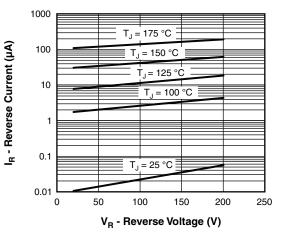


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

Document Number: 96316

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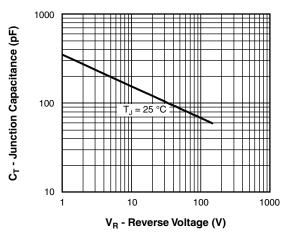


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

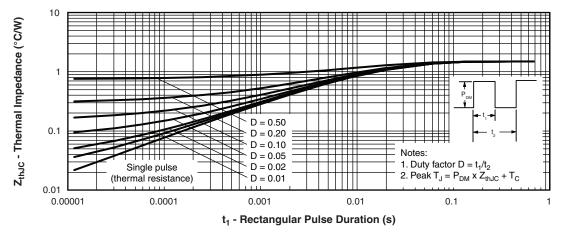
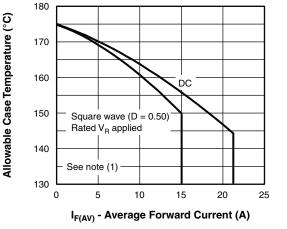
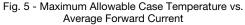
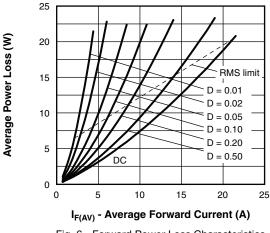


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics







3

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VS-MURB1520-M3, VS-MURB1520-1-M3



Vishay Semiconductors

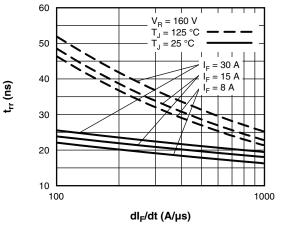
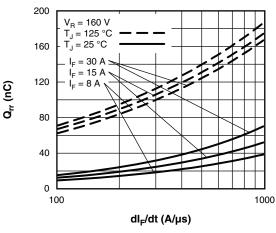


Fig. 7 - Typical Reverse Recovery Time vs. dI_F/dt





Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

Pd = forward power loss = $I_{F(AV)} \times V_{FM}$ at ($I_{F(AV)}/D$) (see fig. 6); Pd_{REV} = inverse power loss = $V_{R1} \times I_R$ (1 - D); I_R at V_{R1} = rated V_R

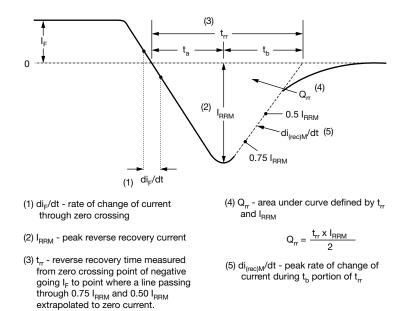
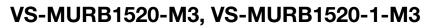
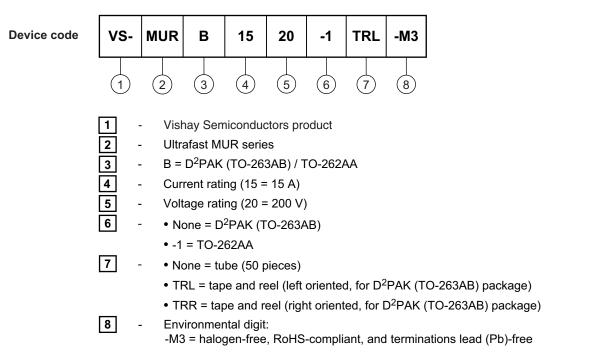


Fig. 9 - Reverse Recovery Waveform and Definitions





ORDERING INFORMATION TABLE

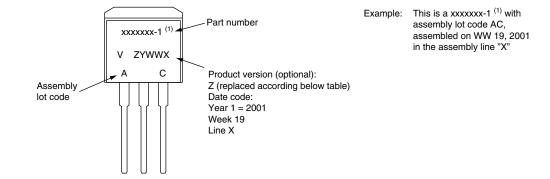


ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-MURB1520-M3	50	1000	Antistatic plastic tube				
VS-MURB1520TRR-M3	800	800	13" diameter reel				
VS-MURB1520TRL-M3	800	800	13" diameter reel				
VS-MURB1520-1-M3	50	1000	Antistatic plastic tube				

LINKS TO RELATED DOCUMENTS						
Dimensions	D ² PAK (TO-263AB)	www.vishay.com/doc?96164				
Differsions	TO-262AA	www.vishay.com/doc?96165				
Part marking information	D ² PAK (TO-263AB)	www.vishay.com/doc?95444				
Part marking information	TO-262AA	www.vishay.com/doc?95443				
Packaging information		www.vishay.com/doc?96424				
SPICE model		www.vishay.com/doc?95271				



TO-262



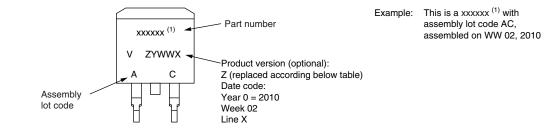
Note

⁽¹⁾ If part number contain "H" as last digit, product is AEC-Q101 qualified

ENVIRONMENTAL NAMING CODE (Z)	PRODUCT DEFINITION			
A Termination lead (Pb)-free				
B Totally lead (Pb)-free				
E	RoHS-compliant and termination lead (Pb)-free			
F	RoHS-compliant and totally lead (Pb)-free			
М	Halogen-free, RoHS-compliant and termination lead (Pb)-free			
N Halogen-free, RoHS-compliant and totally lead (Pb)-free				
G	Green			



D²PAK



Note

⁽¹⁾ If part number contain "H" as last digit, product is AEC-Q101 qualified

ENVIRONMENTAL NAMING CODE (Z) PRODUCT DEFINITION				
A Termination lead (Pb)-free				
В	Totally lead (Pb)-free			
E	RoHS-compliant and termination lead (Pb)-free			
F	RoHS-compliant and totally lead (Pb)-free			
М	Halogen-free, RoHS-compliant, and termination lead (Pb)-free			
N	Halogen-free, RoHS-compliant, and totally lead (Pb)-free			
G	Green			

D²PAK

DIMENSIONS in millimeters and inches



otated	90	Ű
<u>Scale</u>	<u>ə:</u> 8	:1

SYMBOL	MILLIM	ETERS	INCHES		NOTES	
STNIDUL	MIN.	MAX.	MIN.	MAX.	NOTES	
А	4.06	4.83	0.160	0.190		
A1	0.00	0.254	0.000	0.010		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
с	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2]

CVM	BOL	MILLIM	ETERS	INCHES		NOTES
511	BUL	MIN.	MAX.	MIN.	MAX.	NOTES
C)1	6.86	8.00	0.270	0.315	3
E	Ξ	9.65	10.67	0.380	0.420	2, 3
E	1	7.90	8.80	0.311	0.346	3
	e	2.54 BSC		0.100	BSC	
ł	1	14.61	15.88	0.575	0.625	
I	L	1.78	2.79	0.070	0.110	
L	.1	-	1.65	-	0.066	3
L	.2	1.27	1.78	0.050	0.070	
L	.3	0.25 BSC		0.010	BSC	
L	.4	4.78	5.28	0.188	0.208	

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Datum A and B to be determined at datum plane H

⁽⁶⁾ Controlling dimension: inches

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-263AB

Revision: 13-Jul-17

1

Document Number: 96164

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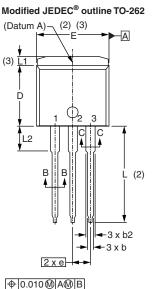
Outline Dimensions

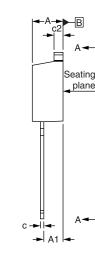


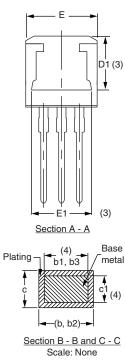
Vishay Semiconductors

TO-262AA

DIMENSIONS in millimeters and inches







1	maan	meath	TRAT



Diodes 1. - Anode (two die)/open (one die) 2., 4. - Cathode 3. - Anode

Lead assignments

SYMBOL	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190	
A1	2.03	3.02	0.080	0.119	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
С	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54 BSC		0.100 BSC		
L	13.46	14.10	0.530	0.555	
L1	-	1.65	-	0.065	3
L2	3.56	3.71	0.140	0.146	

 ⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994
⁽²⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the state back. the outmost extremes of the plastic body

(3) Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only (5)

Controlling dimension: inches

(6) Outline conform to JEDEC® TO-262 except A1 (max.), b (min., max.), b1 (min.), b2 (max.), c (min.), c1(min.), c2 (max.), D (min.), E (max.), L1 (max.), L2 (min., max.)

Revision: 30-Nov-17

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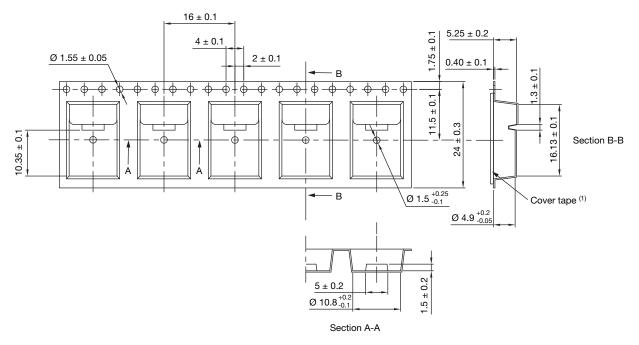
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D²PAK (TO-263AB)

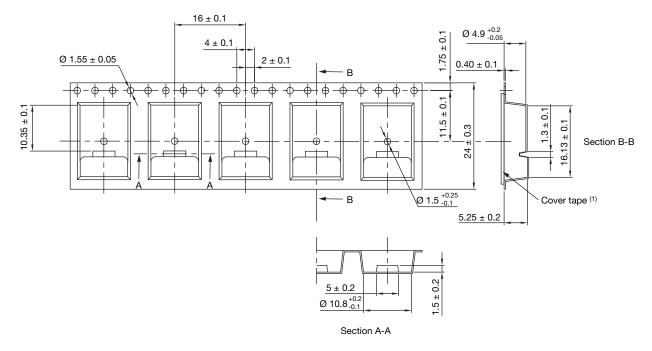
CARRIER TAPE FOR TAPE AND REEL LEFT in millimeters



Note

 $^{\left(1\right)}$ For dimensions, see next pages

CARRIER TAPE FOR TAPE AND REEL RIGHT in millimeters



Note

⁽¹⁾ For dimensions, see next pages

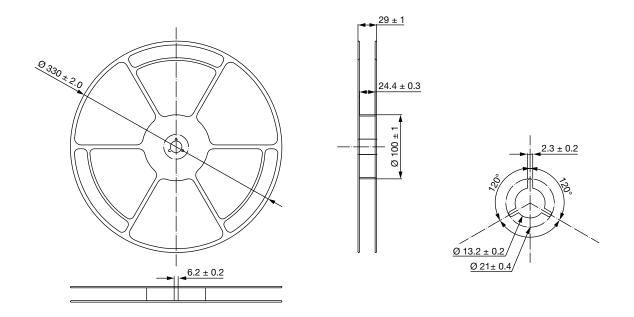
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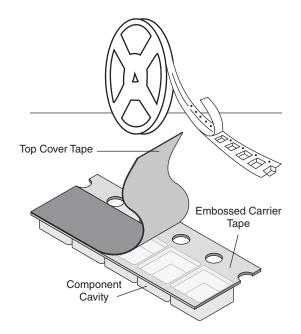
Packaging Information

Vishay Semiconductors

REEL FOR CARRIER TAPE in millimeters



CARRIER TAPE AND REEL PACKAGING D²PAK (TO-263AB)

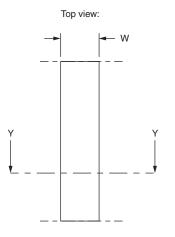


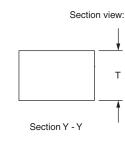
Packaging Information

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COVER TAPE FOR CARRIER TAPE in millimeters





APPLICATION	COVER TAPE WIDTH W	COVER TAPE THICKNESS T	CARRIER TAPE WIDTH	MATERIAL
D ² PAK (TO-263AB)	21.3 ± 0.1	0.060 ± 0.01	24	Antistatic/treated/transparent/polyester



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